L	Hits	Search Text	DB	Time stamp
Number		(11504000011)		
1	2	("5942032").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/04/13 17:02
2	1262	((117/13) or (117/19) or (117/21) or (117/34)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/04/13 17:02
3	17	((((117/13) or (117/19) or (117/21) or (117/34)).CCLS.) and (hydrogen or "H.sub.2") near20 (pressure or vacuum)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/04/13 17:04
4	13	((((117/13) or (117/19) or (117/21) or (117/34)).CCLS.) and (hydrogen or "H.sub.2") near20 (pressure or vacuum) and czochralski	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/04/13 17:13
5	455	(257/620).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/04/13 17:14
6	362	(438/906).CCLS.	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/04/13 17:14
7	0	(437/83).CCLS.	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/04/13 17:14
8	0	(437/84).CCLS.	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/04/13 17:15
9	413	(117/84).CCLS.	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/04/13 17:15
10	1229	((257/620).CCLS.) or ((438/906).CCLS.) or ((437/83).CCLS.) or ((437/84).CCLS.)	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/04/13 17:15
11	4	(((257/620).CCLS.) or ((438/906).CCLS.) or ((437/83).CCLS.) or ((437/84).CCLS.) or ((117/84).CCLS.)) and czochralski and (hydrogen or "H.sub.2") near15 (vacuum or pressure)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/04/13 17:16
-	1154	((257/620) or (438/906) or (437/83) or (437/84) or (117/19) or (117/84)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/04/11 18:01
-	1	((("257/620") or ("438/906") or ("437/83") or ("437/84") or ("117/19") or ("117/84")).CCLS.) and (hydrogen with dop\$3 with silicon with wafer) same concentration	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/01/05 19:09

-	90	((("257/620") or ("438/906") or ("437/83") or ("437/84") or ("117/19") or	USPAT;	2002/01/05
		("117/84")).CCLS.) and czochralski	US-PGPUB; EPO; JPO;	19:10
		(== , == , , , ==== , and ===================================	DERWENT;	
			IBM_TDB	
-	18		USPAT;	2002/01/05
		("437/83") or ("437/84") or ("117/19") or ("117/84")).CCLS.) and heat adj shield	US-PGPUB; EPO; JPO;	19:11
		(117701 //.colb.) and heat adj shield	DERWENT;	
Ì			IBM_TDB	
-	37		USPAT;	2002/01/05
İ		("437/83") or ("437/84") or ("117/19") or ("117/84")).CCLS.) and nitrogen with	US-PGPUB; EPO; JPO;	19:11
		dop\$3	DERWENT;	
		_	IBM_TDB	
-	43		USPAT;	2002/01/05
		("437/83") or ("437/84") or ("117/19") or ("117/84")).CCLS.) and (argon with	US-PGPUB; EPO; JPO;	19:12
		hydrogen)	DERWENT;	
			IBM_TDB	
_	201		USPAT;	2002/01/05
		("437/83") or ("437/84") or ("117/19") or ("117/84")).CCLS.) and oxidation	US-PGPUB; EPO; JPO;	19:12
		(11// 01 // 100101/ and Oxidation	DERWENT;	
			IBM_TDB	
_	1	single adj silicon adj crystal.ti,ab. and czochralski.ti,ab. and nitrogen.ti,ab.	USPAT;	2002/01/05
		czochraiski.ci,ab. and hitrogen.ti,ab.	US-PGPUB; EPO; JPO;	19:14
			DERWENT;	
	54		IBM_TDB	
-	34	silicon adj single adj crystal.ti,ab. and czochralski.ti,ab. and nitrogen.ti,ab.	USPAT; US-PGPUB;	2002/01/05
		description and merogen.cr, ab.	EPO; JPO;	19.14
			DERWENT;	
_	805	(117/13).CCLS.	IBM_TDB	2000/01/05
		(117/13).0013.	USPAT; US-PGPUB;	2002/01/05
			EPO; JPO;	13.17
			DERWENT;	
_	o	(("117/13").CCLS.) and heat adj	<pre>IBM_TDB USPAT;</pre>	2002/01/05
		sjield.ti,ab. and czochralski	US-PGPUB;	19:17
			EPO; JPO;	
			DERWENT;	
_	5	(("117/13").CCLS.) and heat adj	<pre>IBM_TDB USPAT;</pre>	2002/01/05
		shield.ti,ab. and czochralski	US-PGPUB;	19:17
			EPO; JPO;	
			DERWENT; IBM TDB	
-	43	trench adj mosfet.ti.	USPAT;	2002/01/05
		-	US-PGPUB;	20:15
			EPO; JPO;	
			DERWENT; IBM TDB	
-	9	(trench adj mosfet.ti.) and 257/\$6.ccls.	USPAT;	2002/01/05
			US-PGPUB;	20:15
			EPO; JPO;	
			DERWENT; IBM TDB	
_	4	"6191009"	USPAT;	2002/01/29
			US-PGPUB;	12:24
		ļ	EPO; JPO; DERWENT;	
			IBM TDB	
-	5	(("6191009") or ("6299982") or	USPAT	2002/01/29
		("5942032") or ("6224668") or		12:25
_	5	("6197109")).PN. (("6191009") or ("6299982") or	USPAT	2002/02/01
		("5942032") or ("6244668") or	OULHI	11:22
		("6197109")).PN.		

	T	/#C004CC0#) PY	· · · · · · · · · · · · · · · · · · ·	
-	1	("6224668").PN.	USPAT	2002/02/01 11:29
-	4	("4210486").PN.	USPAT;	2002/06/11
			US-PGPUB;	16:22
			EPO; JPO;	
			DERWENT;	
_	410	(liquid adj crystal adj display or	IBM_TDB	2002/06/11
	410	lcd).ti. and 257/\$6.ccls.	USPAT; US-PGPUB;	2002/06/11
		201, 1021 and 201, 4010015.	EPO; JPO;	10.25
			DERWENT;	
			IBM_TDB	
-	64	method.clm. and silicon.ti, ab. and	USPAT;	2002/06/19
		wafer.clm. and melt.clm. and (h or hydrogen).clm. and (pressure near4 mbar)	US-PGPUB; EPO; JPO;	17:56
		(nitrogen near4 (doping or dopant or	DERWENT;	
ļ		doped or dope)) and	IBM TDB	
		czochralski.ti,ab,clm.	_	
_	64		USPAT;	2002/06/19
		wafer.clm. and melt.clm. and hydrogen.clm. and (pressure near4 mbar)	US-PGPUB;	17:59
		(nitrogen near4 (doping or dopant or	EPO; JPO; DERWENT;	
		doped or dope)) and	IBM TDB	
		czochralski.ti,ab,clm.	_	
-	1	method.clm. and silicon.ti,ab. and	USPAT;	2002/06/19
		wafer.clm. and melt.clm. and hydrogen.clm. and (pressure near4 mbar)	US-PGPUB;	18:01
		and (nitrogen near4 (doping or dopant or	EPO; JPO; DERWENT;	
		doped or dope)) and	IBM TDB	
		czochralski.ti,ab,clm.	,	
_	1	method.clm. and silicon.ti,ab. and	USPAT;	2002/06/19
		wafer.clm. and melt.clm. and (h or hydrogen).clm. and (pressure near4 mbar)	US-PGPUB;	18:02
		and (nitrogen near4 (doping or dopant or	EPO; JPO; DERWENT;	
		doped or dope)) and	IBM TDB	
		czochralski.ti,ab,clm.	_	
-	1	method.clm. and silicon.ti,ab. and	USPAT;	2002/06/19
		wafer.clm. and (h or hydrogen).clm. and (pressure near4 mbar) and (nitrogen near4	US-PGPUB; EPO; JPO;	18:03
		(doping or dopant or doped or dope)) and	DERWENT;	
		czochralski.ti,ab,clm.	IBM TDB	
-	1	method.clm. and silicon.ti,ab. and (h or	USPAT;	2002/06/19
		hydrogen).clm. and (pressure near4 mbar) and (nitrogen near4 (doping or dopant or	US-PGPUB;	18:03
		doped or dope)) and	EPO; JPO; DERWENT;	
		czochralski.ti,ab,clm.	IBM TDB	
-	1	silicon.ti,ab. and (h or hydrogen).clm.	USPAT;	2002/06/19
		and (pressure near4 mbar) and (nitrogen	US-PGPUB;	18:04
		<pre>near4 (doping or dopant or doped or dope)) and czochralski.ti,ab,clm.</pre>	EPO; JPO;	
		aopo,, and chocitaiski.ti, ab, Cim.	DERWENT; IBM TDB	
-	1	silicon and (h or hydrogen).clm. and	USPAT;	2002/06/19
		(pressure near4 mbar) and (nitrogen near4	US-PGPUB;	18:05
		(doping or dopant or doped or dope)) and	EPO; JPO;	
		czochralski.ti,ab,clm.	DERWENT;	
_	1	silicon and (h or hydrogen) and (pressure	<pre>IBM_TDB USPAT;</pre>	2002/06/19
	-	near4 mbar) and (nitrogen near4 (doping	US-PGPUB;	18:06
		or dopant or doped or dope)) and	EPO; JPO;	
}		czochralski.ti,ab,clm.	DERWENT;	
_	1	silicon and (h or hydrogen) and (pressure	IBM_TDB	2002/06/12
	1	near4 mbar) and (nitrogen near4 (doping	USPAT; US-PGPUB;	2002/06/19 18:06
		or dopant or doped or dope)) and	EPO; JPO;	10.00
	ŀ	czochralski	DERWENT;	
			IBM_TDB	
-	1	silicon and (h or hydrogen) and (pressure near5 mbar) and (nitrogen near5 (doping	USPAT;	2002/06/19
	Į	or dopant or doped or dope)) and	US-PGPUB; EPO; JPO;	18:07
		czochralski	DERWENT;	
			IBM_TDB	

-	22		USPAT;	2002/06/19
ļ		and (nitrogen near5 (doping or dopant or	US-PGPUB;	19:20
		doped or dope)) and czochralski	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
_	5	The state of the s	USPAT;	2002/06/19
		oxygen	US-PGPUB;	19:21
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	23	czochralski.ti,ab. and pressure near3	USPAT;	2002/06/19
		argon	US-PGPUB;	20:37
1			EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	5	czochralski.ti,ab. and pressure near3	USPAT;	2002/06/19
		argon near3 mbar	US-PGPUB;	20:37
			EPO; JPO;	20.37
			DERWENT;	
	}		IBM TDB	ľ
_	1 0	czochralski.ti,ab. and pressure near3	USPAT;	2002/06/19
		argon near3 mbar near3 hydrogen	US-PGPUB;	2002/06/19
		1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1	EPO; JPO;	20.30
	1		DERWENT;	
_	3	czochralski.ti,ab. and pressure near3	IBM_TDB USPAT;	2002/06/19
	1	mbar near3 hydrogen	US-PGPUB;	2002/06/19
		mout mouts mydrogen	l .	20:38
			EPO; JPO;	
	i		DERWENT;	
_	3	czochralski.ti,ab. and pressure near3	IBM_TDB	2002/06/10
		mbar near3 hydrogen and silicon.ti,ab.	USPAT;	2002/06/19
		mbar hears hydrogen and silicon.cl, ab.	US-PGPUB;	20:39
			EPO; JPO;	
			DERWENT;	
_	3	czochralski.ti,ab. and pressure near3	IBM_TDB	222242542
	3	mbar near3 argon and silicon.ti,ab.	USPAT;	2002/06/19
		mbar nears argon and silicon.ti,ab.	US-PGPUB;	20:39
			EPO; JPO;	
			DERWENT;	
_	13	czochralski and (noble or inert or argon)	IBM_TDB	0000/04/00
	15	near4 mbar	USPAT;	2002/06/20
		neary mbar	US-PGPUB;	13:51
			EPO; JPO;	
			DERWENT;	
_	2	("6291874").PN.	IBM_TDB	2222 (25 (25
		\ \ \OZJIOTI \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \	USPAT;	2002/06/20
			US-PGPUB;	14:11
			EPO; JPO;	
			DERWENT;	
_	2	("6200902") DM	IBM_TDB	
i	4	("6299892").PN.	USPAT;	2002/06/20
			US-PGPUB;	15:37
			EPO; JPO;	[
			DERWENT;	
	ء ا	James describes as a second se	IBM_TDB	
-	3	(zone-drawing or zone adj drawing) near12	USPAT;	2002/06/20
		czochralski	US-PGPUB;	16:07
ļ			EPO; JPO;	
İ	ļ		DERWENT;	
			IBM_TDB	
-	6	(("6291874") or ("4330361")).PN.	USPAT;	2002/06/20
			US-PGPUB;	16:07
	[EPO; JPO;	
	ĺ		DERWENT;	
	ļ		IBM TDB	
-	2	("6291874").PN.	USPAT;	2002/12/05
			US-PGPUB;	20:43
			EPO; JPO;	
	ļ		DERWENT;	
			IBM TDB	

	T		_	
_	3	("4330361").PN.	USPAT;	2002/12/05
			US-PGPUB;	21:05
			EPO; JPO;	
			DERWENT;	[
_	41	pulling near3 czochralski near12 melting	IBM_TDB	2002/12/05
	1	pariting hears czochrarski heariz mercing	USPAT; US-PGPUB;	2002/12/05
			EPO; JPO;	21:13
			DERWENT;	
			IBM TDB	
_	0	Learning modern orocitrary in incarry mercring	USPAT;	2002/12/05
		near12 pressure	US-PGPUB;	21:13
			EPO; JPO;	-1.13
			DERWENT;	
			IBM TDB	
-	1		USPAT;	2002/12/05
		near17 pressure	US-PGPUB;	21:13
			EPO; JPO;	
			DERWENT;	
_	2	/#C20020C#\\ PY	IBM_TDB	
_	2	("6388286").PN.	USPAT;	2002/12/06
			US-PGPUB;	12:18
	1		EPO; JPO;	
			DERWENT;	
_	2	("6194283").PN.	IBM_TDB USPAT;	2002/12/06
		, , , , , , , , , , , , , , , , , , , ,	USPAT; US-PGPUB;	2002/12/06
			EPO; JPO;	12:10
			DERWENT;	
			IBM TDB	
-	2	("4890144").PN.	USPAT;	2002/12/06
			US-PGPUB;	12:20
			EPO; JPO;	
			DERWENT;	
		(# 600000	IBM_TDB	
	2	("6323090").PN.	USPAT;	2002/12/06
			US-PGPUB;	12:20
			EPO; JPO;	
			DERWENT;	
_	0	("hydrogen near2 pressure and	IBM_TDB	0000/04/11
	Ü	czochralski.it,ab.").PN.	USPAT;	2003/04/11
		OZOGITATIONIC, AD.).FN.	US-PGPUB;	18:01
			EPO; JPO; DERWENT;	
			IBM TDB	
-	4	hydrogen near2 pressure and	USPAT;	2003/04/11
		czochralski.ti,ab.	US-PGPUB;	18:02
			EPO; JPO;	= • • • •
l			DERWENT;	
			IBM_TDB	
-	5	(single-crystalline or	USPAT;	2003/04/12
		single-crystal) ti, ab, clm. and stacking	US-PGPUB;	13:33
		adj fault.ti,ab,clm. and (pressure or	EPO; JPO;	
		vacuum) and (hydrogen or "H.sub.2")	DERWENT;	
_	185	/single-crystalli	IBM_TDB	
	103	(single-crystalline or	USPAT;	2003/04/12
		single-crystal).ti,ab,clm. and (growth or growing).ti,ab,clm. and (pressure or	US-PGPUB;	13:34
		vacuum) and (hydrogen or "H.sub.2")	EPO; JPO;	
		vacadam, and (mydrogen or "H. sub. 2")	DERWENT;	
_	o l	(single-crystalline or	<pre>IBM_TDB USPAT;</pre>	2002/04/12
Ì	1	single-crystal).ti,ab,clm. and (growth or	US-PGPUB;	2003/04/12 13:35
1		growing).ti,ab,clm. and (pressure or	EPO; JPO;	13.33
	1	vacuum) and (hydrogen or "H.sub.2")	DERWENT;	
	ļ	near12 (mbar or Hg)	IBM TDB	
-	0	(single-crystalline or	USPAT;	2003/04/12
ŀ		single-crystal).ti,ab,clm. and (growth or	US-PGPUB;	13:35
		growing).ti,ab,clm. and (pressure or	EPO; JPO;	-3.00
		vacuum) and (hydrogen or "H.sub.2")	DERWENT;	
		near12 (mbar or mtorr or Hg)	IBM TDB	
	J	- (or medit of fig)	TOLI TOR	

Single adj crystal or monocrystal).tl.ab.clm. and (growth or growing).tl.ab.clm. and (pressure or vacuum) and (hydrogen or "H. sub.2") Testar					
vacuum) and (hydrogen or "H.sub.2") hear12 (man or mator or Hg) (single-crystal) into or single-crystal or single adj crystal or monocrystal).ti, ab, clm. and (growth or growing).ti, ab, clm. and	_	22	single adj crystal or monocrystal).ti,ab,clm. and (growth or	US-PGPUB; EPO; JPO;	
single adj crystal or monocrystal). ti, ab, clm. and (growth or growing). ti, ab, clm. and (pressure or vacuum) and (hydrogen or "H. sub.2") near12 (atm or pascal or mbar or mtorr or Hg) 1 (single-crystalline or single-crystal or single adj crystal or monocrystal). ti, ab, clm. and (growth or growing). ti, ab, clm. and (growth or gro		35	vacuum) and (hydrogen or "H.sub.2") near12 (mbar or mtorr or Hg)	IBM_TDB	
single adj crystal or single-crystal or single adj crystal or monocrystal).ti,ab,clm. and (growth or growing).ti,ab,clm. and (pressure or vacuum) and (hydrogen or "H. sub.2") near12 (atm or pascal or monocrystal) or single adj crystal or monocrystal).ti,ab,clm. and (growth or growing).ti,ab,clm. and (pressure or vacuum) and (hydrogen or "H. sub.2") near12 (atm or pascal or monocrystal) or single adj crystal or monocrystal or crockralaki).ti,ab,clm. and (growth or single adj crystal or monocrystal or crockralaki).ti,ab,clm. and (growth or single adj crystal or monocrystal or crockralaki).ti,ab,clm. and (growth or yacuum) and (hydrogen or "H. sub.2") near12 (atm or pascal or monocrystal or crockralaki).ti,ab,clm. and (growth or growing).ti,ab,clm. and (growth or growing).ti,ab,		33	single adj crystal or monocrystal).ti,ab,clm. and (growth or growing).ti,ab,clm. and (pressure or vacuum) and (hydrogen or "H.sub.2") near12 (atm or pascal or mbar or mtorr or	US-PGPUB; EPO; JPO; DERWENT;	
Single adj crystal or single-crystal or single adj crystal or monocrystal).ti, ab, clm. and (growth or growing).ti, ab, clm. and (growth or nearl2 (atm or pascal or mbar or mtorr or Hg) and nitrogen nearl2 (doping or impurity or doped) 1 (single-crystalline or single-crystal or single adj crystal or monocrystal or czochralski).ti, ab, clm. and (growth or growing).ti, ab, clm. and (pressure or vacuum) and (hydrogen or "H. sub. 2") nearl2 (atm or pascal or mbar or mtorr or Hg) and nitrogen nearl2 (doping or impurity or doped) 2 (single-crystalline or single-crystal or single adj crystal or monocrystal or czochralski).ti, ab, clm. and (growth or growing).ti, ab, clm. and (pressure or vacuum) and (hydrogen or "H. sub. 2") nearl5 (atm or pascal or mbar or mtorr or Hg) and ("n. sub.2" or nitrogen) nearl5 (doping or impurity or doped or impurities) 3 (single-crystalline or single-crystal or single adj crystal or monocrystal or czochralski).ti, ab, clm. and (growth or growing).ti, ab, clm. and (_	0	(single-crystalline or single-crystal or single adj crystal or monocrystal).ti,ab,clm. and (growth or growing).ti,ab,clm. and (pressure or vacuum) and (hydrogen or "H.sub.2") near12 (atm or pascal or mbar or mtorr or Hg) and nitrogen near12 (doping or	US-PGPUB; EPO; JPO; DERWENT;	
Single-crystalline or single-crystal or single adj crystal or monocrystal or czochralski).ti,ab,clm. and (growth or growing).ti,ab,clm. and (growth or gro	_	1	(single-crystalline or single-crystal or single adj crystal or monocrystal).ti,ab,clm. and (growth or growing).ti,ab,clm. and (pressure or vacuum) and (hydrogen or "H.sub.2") near12 (atm or pascal or mbar or mtorr or Hg) and nitrogen near12 (doping or	US-PGPUB; EPO; JPO; DERWENT;	
Comple-crystalline or single-crystal or single adj crystal or monocrystal or czochralski).ti,ab,clm. and (growth or growing).ti,ab,clm. and (growth or growing).ti,ab,clm. and (growth or Hg) and ("n.sub.2" or nitrogen) near15 (doping or impurity or doped or impurities) 996	-	1	(single-crystalline or single-crystal or single adj crystal or monocrystal or czochralski).ti,ab,clm. and (growth or growing).ti,ab,clm. and (pressure or vacuum) and (hydrogen or "H.sub.2") near12 (atm or pascal or mbar or mtorr or Hg) and nitrogen near12 (doping or	US-PGPUB; EPO; JPO; DERWENT;	
single adj crystal or monocrystal or czochralski).ti,ab,clm. and (growth or growing).ti,ab,clm. and (pressure or vacuum) and (hydrogen or "H.sub.2") 551 (single-crystalline or single-crystal or single adj crystal or monocrystal or czochralski).ti,ab,clm. and (growth or growing).ti,ab,clm. and (pressure or vacuum) and (hydrogen or "H.sub.2") and silicon.ti,ab,clm. 240 (single-crystalline or single-crystal or single adj crystal or monocrystal or czochralski).ti,ab,clm. and (growth or growing).ti,ab,clm. and (growth or growing).ti,ab,clm. and (pressure or vacuum) and (hydrogen or "H.sub.2").ti,ab,clm. and (growth or growing).ti,ab,clm. and (growth or single-crystalline or single-crystal or single adj crystal or monocrystal or czochralski).ti,ab,clm. and (growth or single adj crystal or monocrystal or czochralski).ti,ab,clm. and (growth or growing).ti,ab,clm. and (growth or growin	-	2	(single-crystalline or single-crystal or single adj crystal or monocrystal or czochralski).ti,ab,clm. and (growth or growing).ti,ab,clm. and (pressure or vacuum) and (hydrogen or "H.sub.2") near15 (atm or pascal or mbar or mtorr or Hg) and ("n.sub.2" or nitrogen) near15 (doping or impurity or doped or impurities)	US-PGPUB; EPO; JPO; DERWENT;	
Single adj crystal or single-crystal or single adj crystal or monocrystal or czochralski).ti,ab,clm. and (growth or yacuum) and (hydrogen or "H.sub.2") and silicon.ti,ab,clm. (single-crystalline or single-crystal or single adj crystal or monocrystal or czochralski).ti,ab,clm. and (growth or growing).ti,ab,clm. and (growth or yacuum) and (hydrogen or "H.sub.2").ti,ab,clm. and silicon.ti,ab,clm. and silicon.ti,ab,clm. and silicon.ti,ab,clm. and silicon.ti,ab,clm. and (growth or yacuum) and (hydrogen or "H.sub.2").ti,ab,clm. and silicon.ti,ab,clm. and (growth or single adj crystal or monocrystal or czochralski).ti,ab,clm. and (growth or growing).ti,ab,clm. and (growth or growing).ti,ab,clm. and (growth or growing).ti,ab,clm. and (pressure or vacuum) and (hydrogen or yacuum) and yacuum) and yacuum and y	-		single adj crystal or monocrystal or czochralski).ti,ab,clm. and (growth or growing).ti,ab,clm. and (pressure or vacuum) and (hydrogen or "H.sub.2")	US-PGPUB; EPO; JPO; DERWENT;	
- 240 (single-crystalline or single-crystal or single adj crystal or monocrystal or czochralski).ti,ab,clm. and (growth or growing).ti,ab,clm. and (pressure or "H.sub.2").ti,ab,clm. and silicon.ti,ab,clm. 5 (single-crystalline or single-crystal or single adj crystal or monocrystal or czochralski).ti,ab,clm. and (growth or growing).ti,ab,clm. and (pressure or yacuum) and (hydrogen or yacuum) and (hydrogen or yacuum) and (hydrogen or yacuum) and (hydrogen or yacuum) and (hydrogen or yacuum) and (hydrogen or yacuum) yacuum) and (hydrogen or yacuum) yacuum) yacuum y		551	(single-crystalline or single-crystal or single adj crystal or monocrystal or czochralski).ti,ab,clm. and (growth or growing).ti,ab,clm. and (pressure or vacuum) and (hydrogen or "H.sub.2") and	USPAT; US-PGPUB; EPO; JPO; DERWENT;	
5 (single-crystalline or single-crystal or single adj crystal or monocrystal or USPAT; 2003/04/12 single adj crystal or monocrystal or US-PGPUB; 23:48 czochralski).ti,ab,clm. and (growth or growing).ti,ab,clm. and (pressure or perwent; vacuum) and (hydrogen or IBM TDB	-	240	(single-crystalline or single-crystal or single adj crystal or monocrystal or czochralski).ti,ab,clm. and (growth or growing).ti,ab,clm. and (pressure or vacuum) and (hydrogen or "H.sub.2").ti,ab,clm. and	US-PGPUB; EPO; JPO; DERWENT;	
pascal or mtorr) and silicon.ti,ab,clm.	-		(single-crystalline or single-crystal or single adj crystal or monocrystal or czochralski).ti,ab,clm. and (growth or growing).ti,ab,clm. and (pressure or vacuum) and (hydrogen or "H.sub.2").ti,ab,clm. near20 (mbar or	US-PGPUB; EPO; JPO; DERWENT;	

] -	0	czochralski.ti,ab,clm. and (growth or	USPAT;	2003/04/12
		growing).ti,ab,clm. and (pressure or vacuum) and (hydrogen or	US-PGPUB;	13:49
		"H.sub.2").ti,ab,clm. near20 (mbar or	EPO; JPO; DERWENT;	
İ		pascal or mtorr) and silicon.ti,ab,clm.	IBM TDB	
-	0	(czochralski or cz-silicon).ti,ab,clm.	USPAT;	2003/04/12
		and (growth or growing).ti,ab,clm. and	US-PGPUB;	13:53
		(pressure or vacuum) and (hydrogen or	EPO; JPO;	
		"H.sub.2").ti,ab,clm. near20 (mbar or	DERWENT;	
_	68	pascal or mtorr) and silicon.ti,ab,clm. (czochralski or cz-silicon and	IBM_TDB	
	00	single-crystalline or single-crystal or	USPAT;	2003/04/12
		single adj crystal).ti,ab,clm. and	US-PGPUB; EPO; JPO;	13:54
		(growth or growing).ti,ab,clm. and	DERWENT;	
		(pressure or vacuum) near12 (mbar or	IBM TDB	
		pascal or mtorr) and silicon.ti,ab,clm.	_	
-	1207	(czochralski or cz-silicon and	USPAT;	2003/04/12
		single-crystalline or single-crystal or	US-PGPUB;	13:55
		single adj crystal).ti,ab,clm. and (growth or growing).ti,ab,clm. and	EPO; JPO;	
		(pressure or vacuum) near12 (mbar or	DERWENT; IBM TDB	
		pascal or mtorr) stacking adj fault and	TDI1_TDB	
		silicon.ti,ab,clm.		
-	6	(czochralski or cz-silicon and	USPAT;	2003/04/12
		single-crystalline or single-crystal or	US-PGPUB;	13:55
		single adj crystal).ti,ab,clm. and (growth or growing).ti,ab,clm. and	EPO; JPO;	
		(pressure or vacuum) near12 (mbar or	DERWENT;	
		pascal or mtorr) and stacking adj fault	IBM_TDB	
		and silicon.ti,ab,clm.		
_	2	("5993557").PN.	USPAT;	2003/04/12
		•	US-PGPUB;	14:04
			EPO; JPO;	
			DERWENT; IBM TDB	
_	23	(cz-silicon or czochralski).ti,ab,clm.	USPAT;	2003/04/12
		and stacking adj fault and (hydrogen or	US-PGPUB;	14:12
		"H.sub.2") and (pressure or vacuum)	EPO; JPO;	
			DERWENT;	
_	6	(cz-silicon or czochralski).ti,ab,clm.	IBM TDB	2002/24/12
	ľ	and stacking adj fault and (hydrogen or	USPAT;	2003/04/12
		"H.sub.2") and (pressure or vacuum) and	US-PGPUB; EPO; JPO;	14:07
		"shin-etsu"	DERWENT;	
			IBM_TDB	
_	11	(cz-silicon or czochralski).ti,ab,clm.	USPAT;	2003/04/12
		and stacking adj fault and (hydrogen or "H.sub.2") and (pressure or vacuum) and	US-PGPUB;	14:13
		(mbar or bar or atm or pascal or torr or	EPO; JPO; DERWENT;	
		mtorr)	IBM TDB	
_	4	(cz-silicon or czochralski).ti,ab,clm.	USPAT;	2003/04/12
		and stacking adj fault and (hydrogen or	US-PGPUB;	14:17
		"H. sub.2") and (pressure or vacuum)	EPO; JPO;	
		near15 (mbar or bar or atm or pascal or torr or mtorr)	DERWENT;	
_	О	(cz-silicon or czochralski).ti,ab,clm.	IBM_TDB USPAT;	2003/04/12
		and stacking adj fault and (hydrogen or	US-PGPUB;	14:18
		"H.sub.2") near25 (pressure or vacuum)	EPO; JPO;	
		near25 (mbar or bar or atm or pascal or	DERWENT;	
_	7	torr or mtorr)	IBM_TDB	
	'	(cz-silicon or czochralski).ti,ab,clm. and (hydrogen or "H.sub.2") near25	USPAT;	2003/04/12
		(pressure or vacuum) near25 (mbar or bar	US-PGPUB;	14:28
		or atm or pascal or torr or mtorr)	EPO; JPO; DERWENT;	
			IBM_TDB	
-	0	stacking adj fault near15 hydrogen near15	USPAT;	2003/04/12
		(mbar or mtorr or pascal)	US-PGPUB;	14:29
		· ·	EPO; JPO;	
			DERWENT;	
	L		IBM_TDB	

4	stacking adi fault and hydrogen pear15	IISDAT.	2003/04/12
	(mbar or mtorr or pascal)	1	14:30
	, and the publication of publication of the publica	1	14.50
		1	
		_	
80	"shin-etsu" and hydrogen and (czochralski		2003/04/12
			14:31
	,	1	14.51
		1	
		1	
5	"shin-etsu" and hydrogen near15 pressure		2003/04/12
	and (czochralski or cz-silicon)		14:32
	(**************************************	1	14.52
		1	
5	"shin-etsu" and hydrogen near15 pressure		2003/04/12
	and (czochralski or cz-silicon or cz adi		14:32
	method)	· ·	14.52
		1	
3	("4330361").PN.		2003/04/12
	•		18:15
		i '	1 20.20
	80 5	<pre>(mbar or mtorr or pascal) "shin-etsu" and hydrogen and (czochralski or cz-silicon) "shin-etsu" and hydrogen near15 pressure and (czochralski or cz-silicon) "shin-etsu" and hydrogen near15 pressure and (czochralski or cz-silicon or cz adj method)</pre>	(mbar or mtorr or pascal) (mbar or mtorr or pascal) (mbar or mtorr or pascal) (mbar or mtorr or pascal) (mbar or mtorr or pascal) (mbar or mtorr or pascal) (mbar or mtorr or pascal) (spo; JPO; DERWENT; IBM_TDB (mbar or mtorr or pascal) (mbar or mtorr or pascal) (pso; JPO; DERWENT; IBM_TDB (mbar or mtorr or pascal) (mbar or mtorr or pascal) (mbar or mtorr or pascal) (mbar or mtorr or pascal) (mbar or mtorr or pascal) (pso; JPO; DERWENT; IBM_TDB (mathod) (mbar or mtorr or pascal) (pso; JPO; DERWENT; IBM_TDB (mathod) (mbar or mtorr or pascal) (mbar or mtor mtor or cz dept use pascal) (mbar or mtor mtor or cz dept use pascal) (mbar or mtor mtor or cz dept use pascal) (mbar or mtor mtor or cz dept use pascal) (mbar or mtor mtor or cz dept use pascal) (mbar or cz dept use pascal) (mbar or mtor or cz dept use pascal) (mbar or mtor or cz dept use pascal) (mbar or mtor or cz dept use p